

# 6th Generation 1700 V, 5 A Silicon Carbide Schottky Diode

#### **Description**

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-247-2 Marking: C6D05170H

#### **Features**

- $\hbox{ \bullet } \quad \hbox{Low Forward Voltage } (V_F) \ \hbox{Drop with Positive} \\ \hbox{Temperature Coefficient}$
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Low Profile Package with Low Inductance

## **Applications**

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

# **Maximum Ratings** ( $T_c = 25^{\circ}$ C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	1700	V			
DC Blocking Voltage	V <sub>DC</sub>	1700	V			
		21		T <sub>c</sub> = 25 °C		
Continuous Forward Current	I <sub>F</sub>	11		T <sub>c</sub> = 125 °C	Fig. 3	
		7	A	T <sub>c</sub> = 150 °C		
Repetitive Peak Forward Surge Current	I <sub>FRM</sub>	32		T <sub>c</sub> = 25 °C, t <sub>p</sub> = 10 ms, Half Sine Wave		
		19		$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms},  \text{Half Sine Wave}$		
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	87		$T_c = 25 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , Half Sine Wave	Fig. 8	
		73		$T_c = 110 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , Half Sine Wave		
Non-Repetitive Peak Forward Surge Current	I <sub>F,Max</sub>	630		$T_{c} = 25 {}^{\circ}\text{C}, t_{p} = 10 \mu\text{s}, \text{Pulse}$		
		620		$T_c = 110 ^{\circ}\text{C}, t_p = 10 \mu\text{s}, \text{Pulse}$		
Power Dissipation	P <sub>tot</sub>	110	W	T <sub>c</sub> = 25 °C	Fig. 4	
		47		T <sub>c</sub> = 110 °C		
i²t Value	∫ i²t	37	- A <sup>2</sup> s	$T_{c} = 25  ^{\circ}\text{C}, t_{p} = 10  \text{ms}$		
		26		T <sub>c</sub> = 110 °C, t <sub>p</sub> = 10 ms		

## **Electrical Characteristics**

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes	
Forward Voltage		1.45	1.7	V	I <sub>F</sub> = 5 A, T <sub>j</sub> = 25 °C	Fig. 1	
	V <sub>F</sub>	2.0	2.8		I <sub>F</sub> = 5 A, T <sub>j</sub> = 175 °C	Fig. 1	
Reverse Current		2	9	μΑ	V <sub>R</sub> = 1700 V, T <sub>j</sub> = 25 °C	Fig. 2	
	R	12	45		V <sub>R</sub> = 1700 V, T <sub>j</sub> = 175 °C		
Total Capacitive Charge	Q <sub>c</sub>	78		nC	V <sub>R</sub> = 1700 V, T <sub>j</sub> = 25 °C	Fig. 5	
		638			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$		
Total Capacitance	С	34		pF	$V_R = 800 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6	
		34			V <sub>R</sub> = 1700 V, T <sub>j</sub> = 25 °C, f = 1 MHz		
Capacitance Stored Energy	E <sub>c</sub>	51		μJ	V <sub>R</sub> = 1700 V	Fig. 7	

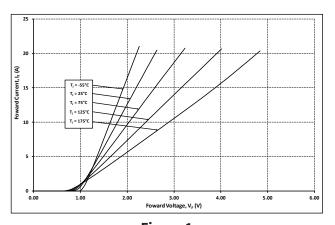
Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

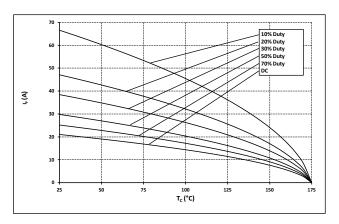
## **Thermal & Mechanical Characteristics**

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R <sub>0, JC (TYP)</sub>	0.95	°C / W	
Thermal Resistance, Junction to Case (Maximum)	R <sub>θ, JC (MAX)</sub>	1.36	°C/W	
Junction Temperature	T <sub>j</sub>	-55 to +175		
Case & Storage Temperature	T <sub>c</sub>	-55 to +150	°C	
Maximum Processing Temperature	T <sub>PROC</sub>	325		10 min max.
TO 247 Manuatina Tanana	-	1	Nm	M3 Screw
TO-247 Mounting Torque		8.8	lbf-in	6-32 Screw

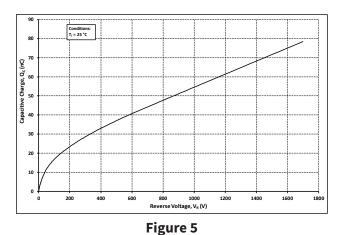
# Typical Performance



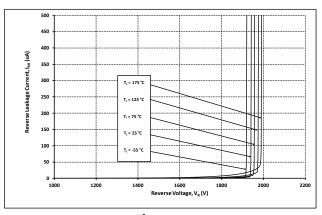
**Figure 1** Forward Characteristics



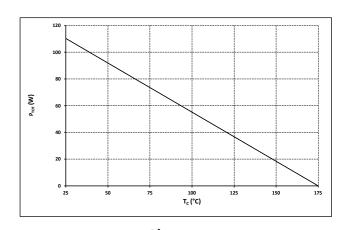
**Figure 3**Current Derating



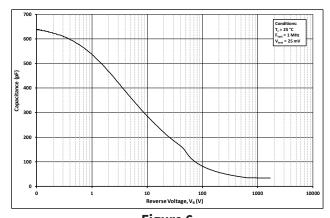
Total Capacitance Charge vs. Reverse Voltage



**Figure 2**Reverse Characteristics

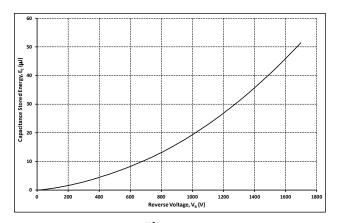


**Figure 4** Power Derating

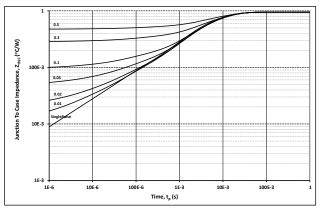


**Figure 6**Capacitance vs. Reverse Voltage

## **Typical Performance**



**Figure 7**Capacitance Stored Energy



**Figure 9**Transient Thermal Impedance

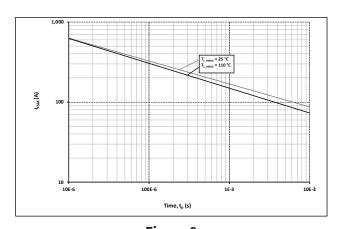


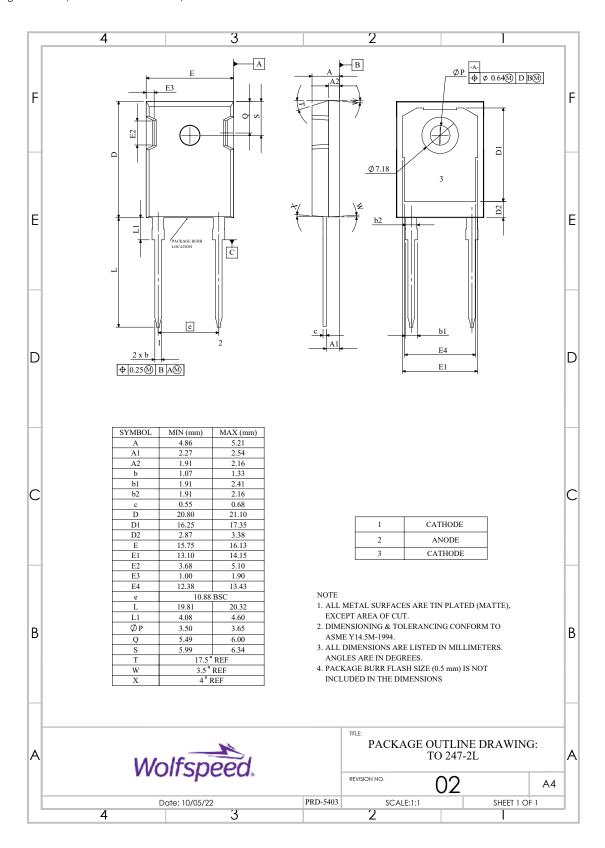
Figure 8

Non-Repetitive Peak Forward Surge Current vs. Pulse Duraion
(Sinusouidal Waveform)

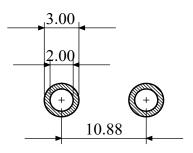
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## **Package Dimensions & Pin-Out**

Package: TO-247-2 (All dimensions are in mm)



# **Recommended Solder Pad Layout**



# **Product Ordering Information**

Order Number	Packing Type
C6D05170H	Tube

 $\label{lem:REACh} \textbf{ReACh}, \textbf{RoHS}, \textbf{and Halogen-Free compliance documentation available for this product}.$ 

# **Revision History**

Document Version	Date of Release	Description of changes
0	November-2022	Initial datasheet

## Notes & Disclaimer

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